Mohamed Henini

List of Publications by Year
in descending order

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846 papers	14,290 citations	28190 55 h-index	43802 91 g-index
882 all docs	882 docs citations	882 times ranked	8135 citing authors

#	Article	IF	Citations
1	From Khoi-San indigenous knowledge to bioengineered CeO2 nanocrystals to exceptional UV-blocking green nanocosmetics. Scientific Reports, 2022, 12, 3468.	1.6	33
2	Analysis of Iâ€“V-T characteristics of Be-doped AlGaAs Schottky diodes grown on (100) GaAs substrates by molecular beam epitaxy. Microelectronics Journal, 2022, 122, 105409.	1.1	9
3	The effect of strain and spatial Bi distribution on the band alignment of GaAsBi single quantum well structure. Physica B: Condensed Matter, 2021, 602, 412487.	1.3	4
4	From cow manure to bioactive carbon dots: a light-up probe for bioimaging investigations, glucose detection and potential immunotherapy agent for melanoma skin cancer. RSC Advances, 2021, 11, 6346-6352.	1.7	15
5	Luminescent MoS₂ Quantum Dots with Tunable Operating Potential for Energy-Enhanced Aqueous Supercapacitors. ACS Omega, 2021, 6, 4542-4550.	1.6	18
6	Structural and optical properties of n-type and p-type GaAs_(1â^'x)Bi _x thin films grown by molecular beam epitaxy on (311)B GaAs substrates. Semiconductor Science and Technology, 2021, 36, 075018.	1.0	0
7	The Role of Defects on the Performance of Quantum Dot Intermediate Band Solar Cells. IEEE Journal of Photovoltaics, 2021, 11, 1022-1031.	1.5	2
8	Investigation of the effect of substrate orientation on the structural, electrical and optical properties of n-type GaAs1â^'xBix layers grown by Molecular Beam Epitaxy. Journal of Alloys and Compounds, 2021, 885, 161019.	2.8	4
9	Transformation of polarons into magnetopolarons in GaAs quantum well. Physica E: Low-Dimensional Systems and Nanostructures, 2021, 136, 115019.	1.3	0
10	Optimal identification of Be-doped Al0.29Ga0.71As Schottky diode parameters using Dragonfly Algorithm: A thermal effect study. Superlattices and Microstructures, 2021, 160, 107085.	1.4	3
11	Effects of nitrogen incorporation and thermal annealing on the optical and spin properties of GaPN dilute nitride alloys. Journal of Alloys and Compounds, 2020, 814, 152233.	2.8	3
12	Investigation of the effects of GaAs substrate orientations on the electrical properties of sulfonated polyaniline based heterostructures. Applied Surface Science, 2020, 504, 144315.	3.1	4
13	A comprehensive study on the effects of gamma radiation on the physical properties of a two-dimensional WS₂monolayer semiconductor. Nanoscale Horizons, 2020, 5, 259-267.	4.1	26
14	Investigation of the structural, optical and electrical properties of indium-doped TiO2 thin films grown by Pulsed Laser Deposition technique on low and high index GaAs planes. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2020, 259, 114578.	1.7	9
15	Effect of thermal annealing on the optical and structural properties of (311)B and (001) GaAsBi/GaAs single quantum wells grown by MBE. Journal of Applied Physics, 2020, 127, 125704.	1.1	6
16	Comparative study of various methods for extraction of multi- quantum wells Schottky diode parameters. Journal of Semiconductors, 2020, 41, 102401.	2.0	2
17	Effect of rapid thermal annealing on the electrical properties of dilute GaAsPN based diodes. Semiconductor Science and Technology, 2019, 34, 105009.	1.0	4
18	Role of interface potential barrier, Auger recombination and temporal coherence in In_{0.5}Ga_{0.5}As/GaAs quantum dot-based p-i-n light emitting diodes. Journal Physics D: Applied Physics, 2019, 52, 095102.	1.3	2

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19	A Novel Parameter Identification Approach for Câ€“Vâ€“T Characteristics of Multi-Quantum Wells Schottky Diode Using Ant Lion Optimizer. Russian Microelectronics, 2019, 48, 428-434.	0.1	4
20	Effect of indium doping on the electrical and structural properties of TiO2 thin films used in MOS devices. Journal of Alloys and Compounds, 2019, 775, 202-213.	2.8	17
21	Revealing the nature of low-temperature photoluminescence peaks by laser treatment in van der Waals epitaxially grown WS₂ monolayers. Nanoscale, 2018, 10, 4807-4815.	2.8	29
22	Î³-rays irradiation effects on dielectric properties of Ti/Au/GaAsN Schottky diodes with 1.2%N. Radiation Physics and Chemistry, 2018, 147, 13-17.	1.4	1
23	Experimental evidences of quantum confined 2D indirect excitons in single barrier GaAs/AlAs/GaAs heterostructure using photocapacitance at room temperature. Journal of Applied Physics, 2018, 123, 044305.	1.1	5
24	Influence of reaction time and synthesis temperature on the physical properties of ZnO nanoparticles synthesized by the hydrothermal method. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	1.1	53
25	Novel multifunctional of magnesium ions (Mg++) incorporated calcium phosphate nanostructures. Journal of Alloys and Compounds, 2018, 730, 31-35.	2.8	15
26	Detailed investigation of defect states in Erbium doped In2O3 thin films. Materials Research Bulletin, 2018, 99, 211-218.	2.7	15
27	Simulation of p-type Schottky Diode Based on Al_{0.29}Ga_{0.71}As with Titanium/Gold Schottky Contact. , 2018, , .		2
28	Evaluation on La2O3 garlanded ceria heterostructured binary metal oxide nanoplates for UV/ visible light induced removal of organic dye from urban wastewater. South African Journal of Chemical Engineering, 2018, 26, 49-60.	1.2	124
29	Investigation of optical and electrical properties of erbium-doped TiO2 thin films for photodetector applications. Journal of Materials Science: Materials in Electronics, 2018, 29, 19588-19600.	1.1	18
30	Optical properties of GaAs1â^'xBix/GaAs quantum well structures grown by molecular beam epitaxy on (100) and (311)B GaAs substrates. Semiconductor Science and Technology, 2018, 33, 124015.	1.0	7
31	Effect of growth techniques on the structural, optical and electrical properties of indium doped TiO2 thin films. Journal of Alloys and Compounds, 2018, 766, 194-203.	2.8	17
32	Exciton localization and structural disorder of GaAs_{1â^'x}Bi_x/GaAs quantum wells grown by molecular beam epitaxy on (311)B GaAs substrates. Semiconductor Science and Technology, 2018, 33, 084002.	1.0	5
33	Voltage- and Light-Controlled Spin Properties of a Two-Dimensional Hole Gas in p-Type GaAs/AlAs Resonant Tunneling Diodes. Journal of Electronic Materials, 2018, 47, 1780-1785.	1.0	0
34	SiC polytypes and doping nature effects on electrical properties of ZnO-SiC Schottky diodes. Microelectronic Engineering, 2017, 171, 11-19.	1.1	20
35	Piezoelectric Response to Coherent Longitudinal and Transverse Acoustic Phonons in a Semiconductor Schottky Diode. Physical Review Applied, 2017, 7, .	1.5	2
36	Transition metal titanium (Ti) doped LaFeO 3 nanoparticles for enhanced optical structural and magnetic properties. Journal of Alloys and Compounds, 2017, 712, 870-877.	2.8	96

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37	Enhanced magnetic properties of polymer-magnetic nanostructures synthesized by ultrasonication. Journal of Alloys and Compounds, 2017, 720, 395-400.	2.8	76
38	Fabrication of novel transparent Co 3 O 4 -TiO 2 nanowires p-n heterojunction diodes for multiband photodetection applications. Journal of Alloys and Compounds, 2017, 712, 7-14.	2.8	34
39	Spin Polarization of Carriers in InGaAs Self-Assembled Quantum Rings Inserted in GaAs-AlGaAs Resonant Tunneling Devices. Journal of Electronic Materials, 2017, 46, 3851-3856.	1.0	3
40	Investigation of defects in indium doped TiO 2 thin films using electrical and optical techniques. Journal of Alloys and Compounds, 2017, 698, 883-891.	2.8	16
41	Investigation of electrically active defects in InGaAs quantum wire intermediate-band solar cells using deep-level transient spectroscopy technique. Nanotechnology, 2017, 28, 045707.	1.3	11
42	Characterisation of temperature dependent parameters of multi-quantum well (MQW) Ti/Au/n-AlGaAs/n-GaAs/n-AlGaAs Schottky diodes. Superlattices and Microstructures, 2017, 111, 1010-1021.	1.4	23
43	Impact of doping on the performance of p-type Be-doped Al 0.29 Ga 0.71 As Schottky diodes. Modern Electronic Materials, 2017, 3, 66-71.	0.2	8
44	Rare earth element (REE) lanthanum doped zinc oxide (La: ZnO) nanomaterials: Synthesis structural optical and antibacterial studies. Journal of Alloys and Compounds, 2017, 723, 1155-1161.	2.8	229
45	Polarization resolved photoluminescence in GaAs1â^'xBix/GaAs quantum wells. Journal of Luminescence, 2017, 182, 49-52.	1.5	6
46	Structural Stabilities and Elastic Thermodynamic Properties of SrTe Compound and SrTe1â^'x Ca x Alloy Under High Pressure. Journal of Electronic Materials, 2017, 46, 766-774.	1.0	0
47	Structural and optical properties of diluted magnetic $$hbox {Ga}_{{1-x}}hbox {Mn}_{{x}}$$ Ga 1 - x. Bulletin of Materials Science, 2017, 40, 1355-1359.	0.8	2
48	Decay of coherent acoustic phonons generated by femtosecond pulsed optical excitation and injected in a Wannier-Stark superlattice (Conference Presentation). , 2017, , .		0
49	Negative activation energy and dielectric signatures of excitons and excitonic Mott transitions in quantum confined laser structures. Journal of Applied Physics, 2016, 120, 144304.	1.1	9
50	Photodegradation of organic pollutants RhB dye using UV simulated sunlight on ceria based TiO2 nanomaterials for antibacterial applications. Scientific Reports, 2016, 6, 38064.	1.6	353
51	Effect of 60Co Î³-ray irradiation on electrical properties of Ti/Au/GaAs1â^'xNx Schottky diodes. Current Applied Physics, 2016, 16, 850-858.	1.1	13
52	Hole spin injection from a GaMnAs layer into GaAsâ€“AlAsâ€“InGaAs resonant tunneling diodes. Journal Physics D: Applied Physics, 2016, 49, 165104.	1.3	0
53	Electrical performance of conducting polymer (SPAN) grown on GaAs with different substrate orientations. Applied Surface Science, 2016, 387, 228-236.	3.1	8
54	Surface effects of vapour-liquid-solid driven Bi surface droplets formed during molecular-beam-epitaxy of GaAsBi. Scientific Reports, 2016, 6, 28860.	1.6	33

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55	Surface-Enhanced Raman Spectroscopy Study of 4-ATP on Gold Nanoparticles for Basal Cell Carcinoma Fingerprint Detection. Journal of Electronic Materials, 2016, 45, 2563-2568.	1.0	24
56	Modeling the effect of 1MeV electron irradiation on the performance of n+â€“pâ€“p+ silicon space solar cells. Radiation Physics and Chemistry, 2016, 123, 103-108.	1.4	18
57	A comparative photoluminescence study on Mn-Free GaAs/AlAs and Mn-containing Ga_{1-x}Mn_xAs/AlAs quantum wells (QWs) grown on various orientations by MBE. Philosophical Magazine, 2016, 96, 223-229.	0.7	2
58	Detection of anomalous Hall voltages in ultrahigh-mobility two-dimensional hole gases generated by optical spin orientation. Physical Review B, 2015, 91, .	1.1	0
59	Period of photoconductivity oscillations and charge dynamics of quantum dots in pâ€“iâ€“n GaAs/InAs/AlAs heterojunctions. JETP Letters, 2015, 102, 720-726.	0.4	5
60	Analysis of Deep Level Defects in GaN p-i-n Diodes after Beta Particle Irradiation. Electronics (Switzerland), 2015, 4, 1090-1100.	1.8	10
61	Effect of post-growth annealing treatment on interfacial misfit GaSb/GaAs heterostructures. Journal of Crystal Growth, 2015, 424, 5-10.	0.7	3
62	Rapid thermal annealing: An efficient method to improve the electrical properties of tellurium compensated Interfacial Misfit GaSb/GaAs heterostructures. Superlattices and Microstructures, 2015, 88, 80-89.	1.4	5
63	Nanometre scale 3D nanomechanical imaging of semiconductor structures from few nm to sub-micrometre depths. , 2015, , .		0
64	Spin polarization of carriers in resonant tunneling devices containing InAs self-assembled quantum dots. Superlattices and Microstructures, 2015, 88, 574-581.	1.4	5
65	Visible to infrared low temperature luminescence of Er3+, Nd3+ and Sm3+ in CaSnO3 phosphors. Applied Radiation and Isotopes, 2015, 99, 69-76.	0.7	22
66	Investigation of the effects of gamma radiation on the electrical properties of dilute GaAs1âˆ’xNx layers grown by Molecular Beam Epitaxy. Current Applied Physics, 2015, 15, 1230-1237.	1.1	14
67	Structural and elastic stabilities of InN in both B4 and B1 phases under high pressure using density-functional perturbation theory. Journal of Alloys and Compounds, 2015, 650, 450-457.	2.8	1
68	Numerical simulation of bias and photo stress onÂindiumâ€“galliumâ€“zinc-oxide thin film transistors. Vacuum, 2015, 120, 59-67.	1.6	21
69	Modeling the effect of deep traps on the capacitanceâ€“voltage characteristics of p-type Si-doped GaAs Schottky diodes grown on high index GaAs substrates. Materials Science in Semiconductor Processing, 2015, 36, 156-161.	1.9	9
70	Enhancement of the luminescence intensity by co-doping Mn2+ into Er3+-doped SrAl2O4. Journal of Luminescence, 2015, 163, 17-20.	1.5	13
71	High-performance organic/inorganic hybrid heterojunction based on Gallium Arsenide (GaAs) substrates and a conjugated polymer. Applied Surface Science, 2015, 357, 2189-2197.	3.1	11
72	W line shape in the resistively detected nuclear magnetic resonance. Journal of Physics Condensed Matter, 2015, 27, 275801.	0.7	5

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73	Electrical Behavior of MBE Grown Interfacial Misfit GaSb/GaAs Heterostructures With and Without Te-Doped Interfaces. IEEE Transactions on Electron Devices, 2015, 62, 3980-3986.	1.6	5
74	Mechanism of periodic height variations along self-aligned VLS-grown planar nanostructures. Nanoscale, 2015, 7, 20442-20450.	2.8	6
75	Band gap and partial density of states for ZnO: Under high pressure. Journal of Alloys and Compounds, 2015, 619, 812-819.	2.8	31
76	Voltage controlled electron spin dynamics in resonant tunnelling devices. Journal Physics D: Applied Physics, 2014, 47, 165102.	1.3	1
77	Preface: Seventh International Conference on Low-Dimensional Structures and Devices. , 2014, , .		0
78	Strain and localization effects in InGaAs(N) quantum wells: Tuning the magnetic response. Journal of Applied Physics, 2014, 116, .	1.1	7
79	Raman scattering reveals strong LO-phonon-hole-plasmon coupling in nominally undoped GaAsBi: optical determination of carrier concentration. Optics Express, 2014, 22, 11680.	1.7	23
80	Quantum oscillations in the photocurrent of GaAs/AlAsp-i-ndiodes. Physical Review B, 2014, 89, .	1.1	11
81	Effects of Be acceptors on the spin polarization of carriers in p-i-n resonant tunneling diodes. Journal of Applied Physics, 2014, 116, 054506.	1.1	0
82	Dynamics of electronic transitions and frequency dependence of negative capacitance in semiconductor diodes under high forward bias. Applied Physics Letters, 2014, 105, .	1.5	7
83	Circular polarization in n-type resonant tunneling diodes with Si delta-doping in the quantum well. , 2014, , .		3
84	Magneto-optical properties of GaBiAs layers. Journal Physics D: Applied Physics, 2014, 47, 075103.	1.3	10
85	Thermal annealing effects on the optical and structural properties of (100) GaAs1âˆ'xBix layers grown by Molecular Beam Epitaxy. Superlattices and Microstructures, 2014, 65, 48-55.	1.4	19
86	Deep traps and temperature effects on the capacitance of p-type Si-doped GaAs Schottky diodes on (211) and (311) oriented GaAs substrates. Superlattices and Microstructures, 2014, 65, 319-331.	1.4	9
87	Identification of nitrogen- and host-related deep-level traps in n-type GaNAs and their evolution upon annealing. Journal of Applied Physics, 2014, 116, 013705.	1.1	12
88	Influence of annealing temperature on electrical characteristics of Ti/Au/GaAsN Schottky diode with 0.2% nitrogen incorporation. Materials Science in Semiconductor Processing, 2014, 22, 92-100.	1.9	11
89	Effect of nitrogen incorporation on electrical properties of Ti/Au/GaAsN Schottky diodes. Superlattices and Microstructures, 2014, 71, 225-237.	1.4	16
90	Radioluminescence and photoluminescence characterization of Eu and Tb doped barium stannate phosphor ceramics. Journal of Alloys and Compounds, 2014, 590, 417-423.	2.8	34

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91	Numerical simulation of the response of substrate traps to a voltage applied to the gate of a gallium arsenide field effect transistor. Materials Science in Semiconductor Processing, 2014, 24, 34-39.	1.9	0
92	Effect of gamma radiation on the electrical properties of Polyaniline/silicon carbide heterojunctions. Radiation Measurements, 2014, 71, 402-406.	0.7	10
93	Zinc oxide thin films on silicon carbide substrates (ZnO/SiC): electro-optical properties and electrically active defects. Semiconductor Science and Technology, 2014, 29, 045021.	1.0	14
94	In-situ electrical characterisation of a photodiode during nano-structuring with a focussed ion beam. Applied Physics A: Materials Science and Processing, 2013, 110, 935-941.	1.1	0
95	Solid state synthesis of SrAl2O4:Mn2+ co-doped with Nd3+ phosphor and its optical properties. Journal of Luminescence, 2013, 144, 128-132.	1.5	31
96	Effect of symmetry reduction on the spin dynamics of (001)-oriented GaAs quantum wells. Physical Review B, 2013, 87, .	1.1	13
97	Raman scattering studies of strain effects in (100) and (311)B GaAs1âˆ'xBix epitaxial layers. Journal of Applied Physics, 2013, 114, 193516.	1.1	22
98	Dispersive line shape in the vicinity of the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î½</mml:mi><mml:mo>=</mml:mo><mml:mn>1</mml:mn> Hall state: Coexistence of Knight-shifted and unshifted resistively detected NMR responses. Physical Review B, 2013, 88, .	1.1	12
99	Suppression of electron magnetotunneling between parallel two-dimensional GaAs/InAs electron systems by the correlation interaction. Semiconductors, 2013, 47, 1215-1218.	0.2	0
100	Optical and electrical control of spin polarization of two-dimensional hole gases in p-type resonant tunnelling devices. Journal Physics D: Applied Physics, 2013, 46, 505313.	1.3	2
101	Deep level transient spectroscopy characterisation of defects in AlGaN/Si dual-band (UV/IR) detectors grown by MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 101-104.	0.8	1
102	Photoluminescence intensity enhancement in self-assembled InAs quantum dots grown on (311)B and (100) GaAs substrates and coated with gold nanoparticles. Physica E: Low-Dimensional Systems and Nanostructures, 2013, 54, 233-236.	1.3	6
103	Classical percolation fingerprints in the high temperature regime of the quantum Hall effect. New Journal of Physics, 2013, 15, 083027.	1.2	6
104	Enhancement of activation energies of sharp photoluminescence lines for GaInNAs quantum wells due to quantum confinement. Journal Physics D: Applied Physics, 2013, 46, 402001.	1.3	5
105	Deep-level transient spectroscopy of interfacial states in â€œbuffer-freeâ€•p-i-n GaSb/GaAs devices. Journal of Applied Physics, 2013, 114, 134507.	1.1	12
106	Visualization of wave function of quantum dot at Fermi-edge singularity regime. Journal of Physics: Conference Series, 2013, 456, 012024.	0.3	2
107	Investigation of deep-level defects in conductive polymer on n-type 4H- and 6H-silicon carbide substrates using I-V and deep level transient spectroscopy techniques. Journal of Applied Physics, 2012, 112, .	1.1	14
108	Anomalous optical properties of GaMnAs/AlAs quantum wells grown by molecular beam epitaxy. Journal Physics D: Applied Physics, 2012, 45, 215301.	1.3	6

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109	Magneto-optical investigation of two-dimensional gases in n-type resonant tunneling diodes. Semiconductor Science and Technology, 2012, 27, 015018.	1.0	3
110	Unusual broadening of E0 and E0 + Î”SO transitions in GaAsBi studied by electromodulation spectroscopy. Journal of Applied Physics, 2012, 111, 066103.	1.1	20
111	Scanning capacitance imaging of compressible and incompressible quantum Hall effect edge strips. New Journal of Physics, 2012, 14, 083015.	1.2	31
112	Wetting-layer-pumped continuous-wave surface emitting quantum dot laser. Proceedings of SPIE, 2012, , .	0.8	0
113	Wetting-Layer-Pumped Continuous-Wave Surface-Emitting Quantum-Dot Laser. IEEE Photonics Technology Letters, 2012, 24, 37-39.	1.3	3
114	Subterahertz Acoustical Pumping of Electronic Charge in a Resonant Tunneling Device. Physical Review Letters, 2012, 108, 226601.	2.9	33
115	Luminescence characterization of cerium doped yttrium gadolinium aluminate phosphors. Optical Materials, 2012, 34, 1921-1925.	1.7	26
116	Spin injection in n-type resonant tunneling diodes. Nanoscale Research Letters, 2012, 7, 592.	3.1	4
117	Correlations between the band structure, activation energies of electron traps, and photoluminescence in n-type GaNAs layers. Applied Physics Letters, 2012, 101, 082109.	1.5	19
118	Absorption and photoluminescence spectroscopy of Er³⁺-doped SrAl₂O₄ceramic phosphors. Philosophical Magazine Letters, 2012, 92, 194-201.	0.5	7
119	Barrier height and interface characteristics of Au/Mn₅Ge₃/Ge (1 1 1) Schottky contacts for spin injection. Semiconductor Science and Technology, 2012, 27, 035014.	1.0	16
120	Observation of the anomalous temperature dependence of resonance tunneling through zero-dimensional states in a quantum well with dynamic coulomb interaction between the tunneling channels. JETP Letters, 2012, 96, 529-535.	0.4	1
121	Comparative optical studies of InGaAs/GaAs quantum wells grown by MBE on (100) and (311)A GaAs planes. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1621-1623.	0.8	7
122	Effect of epitaxial layer thickness on the deep level defects in MBE grown nâ€type Al_{0.33}Ga_{0.67}As. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1643-1646.	0.8	0
123	Raman scattering by the E2h and A1(LO) phonons of InxGa1âˆ’xN epilayers (0.25 < x < 0.75) grown by molecular beam epitaxy. Journal of Applied Physics, 2012, 111, 063502.	1.1	25
124	Structural, electronic and vibrational properties of InN under high pressure. Physica B: Condensed Matter, 2012, 407, 1008-1013.	1.3	19
125	Thermal quenching of single localized excitons in GaInNAs layers. Applied Physics Letters, 2011, 98, .	1.5	26
126	Distribution of bismuth atoms in epitaxial GaAsBi. Applied Physics Letters, 2011, 98, 101902.	1.5	38

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127	Spin-split fields in asymmetric (001)-oriented GaAs/Al<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi /><mml:mrow><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:mrow></mml:math>Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â”</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:mrow></mml:math> quantum wells. Physical Review B, 2011, 83, .	1.1	47
128	Improvement of the nutritional quality of foods as a public health tool. Public Health, 2011, 125, 717-724.	1.4	41
129	Ultrafast Acoustic Gating of Photocurrent in Nanodevices With a Quantum Well. AIP Conference Proceedings, 2011, , .	0.3	0
130	Ultrafast Strain-Induced Current in a GaAs Schottky Diode. Physical Review Letters, 2011, 106, 066602.	2.9	29
131	Circular polarization in a non-magnetic resonant tunneling device. Nanoscale Research Letters, 2011, 6, 101.	3.1	2
132	Spin effects in InAs self-assembled quantum dots. Nanoscale Research Letters, 2011, 6, 115.	3.1	2
133	Electrical characterisation of deep level defects in Be-doped AlGaAs grown on (100) and (311)A GaAs substrates by MBE. Nanoscale Research Letters, 2011, 6, 180.	3.1	9
134	Temperature dependence of dark current in a pâ€“iâ€“n photodiode incorporating a resonant tunneling structure. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 210-214.	0.8	1
135	Micro-photoluminescence of GaInNAs layers grown on GaAs substrates of various crystallographic orientations. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1655-1658.	0.8	6
136	Growth and characterization of InGaN for photovoltaic devices. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2460-2462.	0.8	13
137	Synthesis, structural, magnetic and optical properties of nanocrystalline ZnFe2O4. Physica B: Condensed Matter, 2011, 406, 1989-1994.	1.3	84
138	Microwave power generation by magnetic superlattices. Applied Physics Letters, 2011, 99, 242107.	1.5	0
139	Picosecond strain pulses probed by the photocurrent in semiconductor devices with quantum wells. Physical Review B, 2011, 83, .	1.1	11
140	Spin injection from two-dimensional electron and hole gases in resonant tunneling diodes. Applied Physics Letters, 2011, 99, 233507.	1.5	11
141	Deep levels in H-irradiated GaAs1-xNx (xâ€‰<â€‰0.01) grown by molecular beam epitaxy. Journal of Applied Physics, 2011, 110, .	1.1	11
142	Optical Measurement Of The Rashba Coefficient In GaAs/AlGaAs Quantum Wells. , 2010, , .		1
143	Magnetotunneling spectroscopy of polarons in a quantum well of a resonant-tunneling diode. Journal of Experimental and Theoretical Physics, 2010, 111, 220-224.	0.2	3
144	Deep-level Transient Spectroscopy of GaAs/AlGaAs Multi-Quantum Wells Grown on (100) and (311)B GaAs Substrates. Nanoscale Research Letters, 2010, 5, 1948-1951.	3.1	12

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145	Effect of Charge State in Nearby Quantum Dots onÂQuantum Hall Systems. Journal of Low Temperature Physics, 2010, 159, 234-237.	0.6	0
146	Rashba Conduction Band Spin-Splitting for Asymmetric Quantum Well Potentials. Journal of Superconductivity and Novel Magnetism, 2010, 23, 157-159.	0.8	1
147	Effect of annealing on the structural and optical properties of (311)B GaAsBi layers. Applied Surface Science, 2010, 256, 5688-5690.	3.1	16
148	Measurement of a large hole g-factor in two-dimensional hole gases. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 964-966.	1.3	2
149	Cyclotron study of 2DES incorporating QD layer. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 915-917.	1.3	0
150	Intrinsic photoinduced anomalous Hall effect. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 940-943.	1.3	3
151	Photoinduced Anomalous Hall Effect in 2-Dimensional Hole Gases. , 2010, , .		0
152	The Absence Of The Rashba Spin-Splitting In Undoped Asymmetric Quantum Wells. , 2010, , .		0
153	Optical detection of folded mini-zone-edge coherent acoustic modes in a doped GaAs/AlAs superlattice. Physical Review B, 2010, 82, .	1.1	7
154	Structural and optical properties of dilute InAsN grown by molecular beam epitaxy. Journal of Applied Physics, 2010, 108, .	1.1	20
155	Nonlinear birefringence and time-resolved Kerr measurement of spin lifetimes in (110)GaAs/AlyGa1â^'yAsquantum wells. Physical Review B, 2010, 81, .	1.1	11
156	Optical Imaging of Electrical Carrier Injection into Individual InAs Quantum Dots. Physical Review Letters, 2010, 105, 257401.	2.9	6
157	Fermi-edge singularity at tunneling and anisotropic magneto-tunneling in low-dimensional semiconductor structures. Physica Scripta, 2010, 82, 038106.	1.2	5
158	Growth and characterization of ingan for photovoltaic devices. , 2010, , .		2
159	Cyclotron resonance of two-dimensional electron system affected by neighboring quantum dot layer. Applied Physics Letters, 2010, 96, 193110.	1.5	0
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